

# GSDSB5819WSF

## Schottky Diode

### Product Description

Schottky Barrier Diode 40V and 1A

### Features

- Low Forward Voltage

### Mechanical Data

- SOD-323FL Package
- RoHS Compliant and Halogen Free

### Package and Pin Assignment

SOD-323FL		Equivalent Circuit	
Pin	Description	Pin	Description
1	Anode	2	Cathode

### Ordering and Marking Information

GS P/N	Package	Marking	Quantity / Reel
GSDSB5819WSF	SOD-323FL	SL / 	3,000PCS
<b>GSDSB5819WSF</b>			
- <b>Product Code:</b> GSDS5014	- <b>Package Code:</b> WS for SOD-323FL	- <b>Green Level:</b> F for RoHS Compliant and Halogen Free	
<b>Marking Information</b>			
	- <b>Product Code:</b> □□ is SL /  - Band denotes Cathode end		

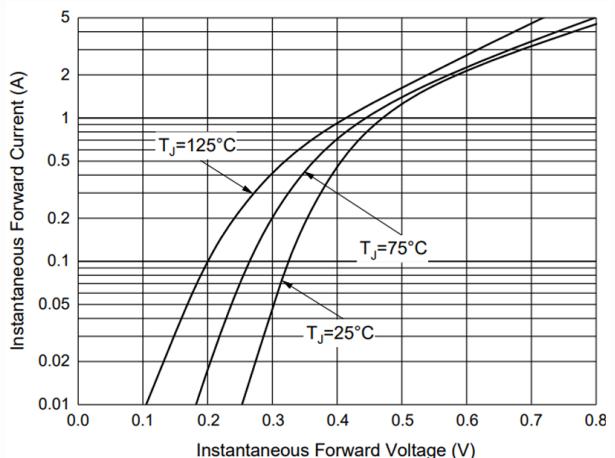
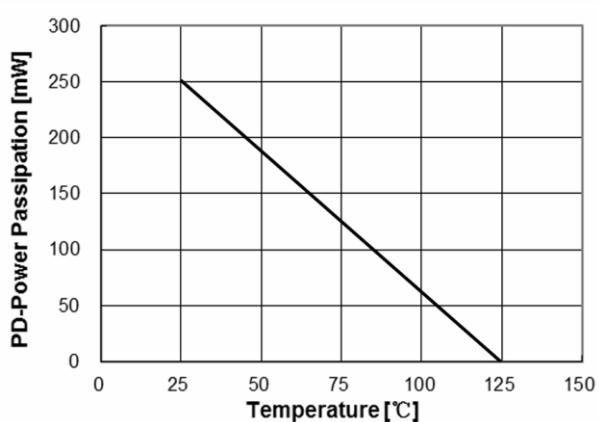
## Absolute Maximum Ratings (T<sub>A</sub>=25°C unless otherwise specified)

Symbol	Parameter	Value	Unit
V <sub>RRM</sub>	Repetitive Peak Reverse Voltage	40	V
V <sub>R(RMS)</sub>	RMS Reverse Voltage	28	V
I <sub>o</sub>	Forward Current	1	A
I <sub>FSM</sub>	Non-Repetitive Peak Forward Current (8.3ms single half sin-wave)	9	A
P <sub>D</sub>	Power Dissipation	250	mW
T <sub>J</sub>	Junction Temperature	125	°C
T <sub>STG</sub>	Storage Temperature Range	-55 to +125	°C

## Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise specified)

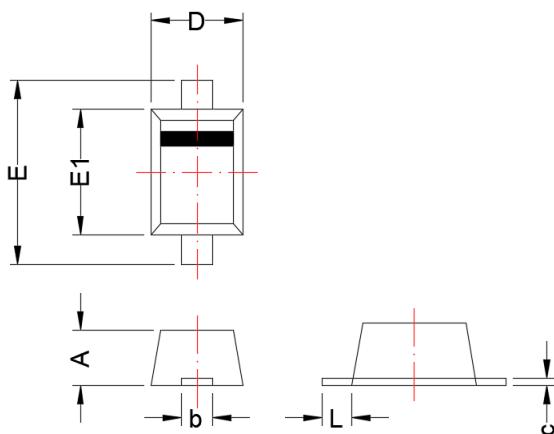
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V <sub>BR</sub>	Breakdown Voltage	I <sub>R</sub> =1mA	40			V
V <sub>F</sub>	Forward Voltage	I <sub>F</sub> =1A			0.6	V
I <sub>R</sub>	Reverse Current	V <sub>R</sub> =40V			1	mA
C <sub>J</sub>	Junction Capacitance	V <sub>R</sub> =4V, f=1MHz			120	pF

## Typical Characteristics ( $T_A=25^\circ\text{C}$ unless otherwise specified)

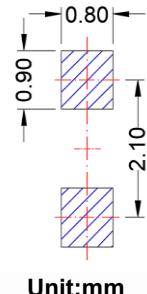


# SOD-323FL

## Package Dimension



## Recommended Land Pattern



## Dimensions

Symbol	Millimeters		Inches	
	Min	Max	Min	Max
A	0.60	1.10	0.023	0.043
b	0.25	0.60	0.010	0.024
c	0.05	0.26	0.002	0.010
D	1.15	1.35	0.045	0.053
E	2.30	2.70	0.091	0.106
E1	1.60	1.80	0.063	0.071
L	0.30	0.50	0.012	0.020

### NOTE:

Dimensions are exclusive of Burrs, Mold Flash & Tie Bar extrusions.

GSDSSB5819WSF

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